

## AMENDMENTS TO THE CLAIMS

1. **(Previously presented)** A resin for a photoresist composition comprising a  $-CR^1R^2OH$  group only at a terminal of a principal chain of the resin; (a1) a structural unit derived from a (meth)acrylate ester having an acid dissociable, dissolution inhibiting group; and (a2) a structural unit derived from a (meth)acrylate ester having a lactone ring, wherein  $R^1$  and  $R^2$  each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of  $R^1$  and  $R^2$  is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups.
2. **(Canceled).**
3. **(Original)** A resin for a photoresist composition according to claim 1, wherein said electron attractive group is a fluorine atom or a fluorinated alkyl group.
4. **(Canceled)**
5. **(Canceled)**
6. **(Canceled)**
7. **(Canceled)**
8. **(Canceled)**
9. **(Previously presented)** A resin for a photoresist composition according to claim 1, further comprising (a3) a structural unit derived from a (meth)acrylate ester having a hydroxyl group.
10. **(Previously presented)** A resin for a photoresist composition according to claim 1, with a weight average molecular weight of no more than 12,000.

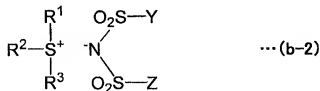
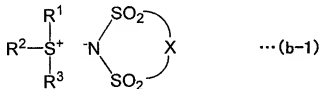
11. **(Previously presented)** A photoresist composition, comprising a resin for a photoresist composition according to claim 1.

12. **(Previously presented)** A photoresist composition comprising:

a resin comprising a  $-\text{CR}^1\text{R}^2\text{OH}$  group only at a terminal of a principal chain of the resin, wherein  $\text{R}^1$  and  $\text{R}^2$  each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of  $\text{R}^1$  and  $\text{R}^2$  is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups; and an acid generator as a component (B).

13. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

14. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), a sulfonium compound represented by either of general formulas (b-1) and (b-2) shown below:



wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom;  $\text{R}^1$  to  $\text{R}^3$  each represent, independently, an aryl group or an alkyl group, and at least one of  $\text{R}^1$  to  $\text{R}^3$  is an aryl group.

15. **(Original)** A photoresist composition according to claim 14, further comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

16. **(Currently amended)** A photoresist composition according to claim 12, further comprising:

~~a resin comprising a  $\text{CR}^1\text{R}^2\text{OH}$  group only at a terminal of a principal chain of the resin, wherein  $\text{R}^1$  and  $\text{R}^2$  each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of  $\text{R}^1$  and  $\text{R}^2$  is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups; and~~

a nitrogen-containing organic compound.

17. **(Currently amended)** A method for forming a resist pattern, comprising the steps of:

applying a photoresist composition that comprises a resin comprising a  $\text{CR}^1\text{R}^2\text{OH}$  group only at a terminal of a principal chain of the resin,  $[[,]]$  wherein  $\text{R}^1$  and  $\text{R}^2$  each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of  $\text{R}^1$  and  $\text{R}^2$  is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups to a surface of a substrate;

performing selective exposure through a desired mask pattern; and

performing developing to form a resist pattern.

18. **(Canceled)**

19. **(Canceled)**

20. **(Canceled)**

21. **(Canceled)**

22. **(Canceled)**

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23. (Canceled)

24. (Canceled)